D44VH10 (NPN), D45VH10 (PNP)

Complementary Silicon Power Transistors

These complementary silicon power transistors are designed for high–speed switching applications, such as switching regulators and high frequency inverters. The devices are also well–suited for drivers for high power switching circuits.

Features

- Fast Switching
- Key Parameters Specified @ 100°C
- Low Collector-Emitter Saturation Voltage
- Complementary Pairs Simplify Circuit Designs
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V _{CEO}	80	Vdc
Collector–Emitter Voltage	V _{CEV}	100	Vdc
Emitter Base Voltage	V _{EB}	7.0	Vdc
Collector Current – Continuous	Ι _C	15	Adc
Collector Current – Peak (Note 1)	I _{CM}	20	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	83 0.67	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Pulse Width \leq 6.0 ms, Duty Cycle \leq 50%.

THERMAL CHARACTERISTICS

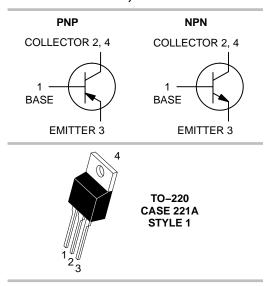
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.5	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62.5	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	ΤL	275	°C



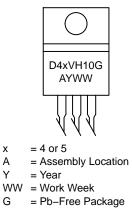
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15 A COMPLEMENTARY SILICON POWER TRANSISTORS 80 V, 83 W



MARKING DIAGRAM



ORDERING INFORMATION

Device	Package	Shipping
D44VH10G	TO-220 (Pb-Free)	50 Units/Rail
D45VH10G	TO-220 (Pb-Free)	50 Units/Rail

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

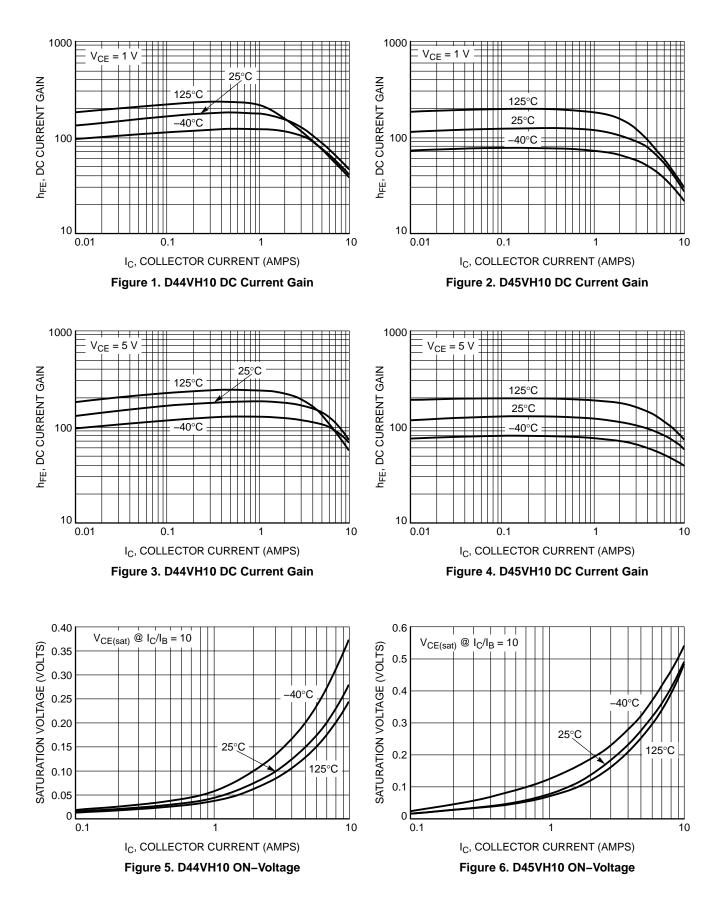
D44VH10 (NPN), D45VH10 (PNP)

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Мах	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (Note 2) $(I_C = 25 \text{ mAdc}, I_B = 0)$	V _{CEO(sus)}	80	_	_	Vdc
	I _{CEV}	- -		10 100	μAdc
Emitter Base Cutoff Current ($V_{EB} = 7.0 \text{ Vdc}, I_C = 0$)	I _{EBO}	_	_	10	μAdc
ON CHARACTERISTICS (Note 2)					
DC Current Gain (I _C = 2.0 Adc, V _{CE} = 1.0 Vdc) (I _C = 4.0 Adc, V _{CE} = 1.0 Vdc)	h _{FE}	35 20			-
Collector–Emitter Saturation Voltage ($I_{C} = 8.0 \text{ Adc}, I_{B} = 0.4 \text{ Adc}$)	V _{CE(sat)}				Vdc
D44VH10		-	-	0.4	
(I _C = 8.0 Adc, I _B = 0.8 Adc) D45VH10 (I _C = 15 Adc, I _B = 3.0 Adc, T _C = 100°C)		-	-	1.0	
D44VH10 D45VH10		-		0.8 1.5	
Base-Emitter Saturation Voltage ($I_C = 8.0 \text{ Adc}, I_B = 0.4 \text{ Adc}$)	V _{BE(sat)}			1.0	Vdc
D44VH10 (I _C = 8.0 Adc, I _B = 0.8 Adc) D45VH10		_	_	1.2 1.0	
$(I_C = 8.0 \text{ Adc}, I_B = 0.4 \text{ Adc}, T_C = 100^{\circ}\text{C})$ D44VH10		_	-	1.1	
(I _C = 8.0 Adc, I _B = 0.8 Adc, T _C = 100°C) D45VH10		_	_	1.5	
DYNAMIC CHARACTERISTICS					
Current Gain Bandwidth Product $(I_C = 0.1 \text{ Adc}, V_{CE} = 10 \text{ Vdc}, f = 20 \text{ MHz})$	f _T	_	50	_	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _C = 0, f _{test} = 1.0 MHz)	C _{ob}				pF
D44VH10 D45VH10		-	120 275		
SWITCHING CHARACTERISTICS					
Delay Time	t _d	_	-	50	ns
Rise Time $(V_{CC} = 20 \text{ Vdc}, I_C = 8.0 \text{ Adc}, I_{B1} = I_{B2} = 0.8 \text{ Adc})$	tr	_	-	250	
Storage Time $(VCC = 20 Vac, 1C = 0.0 Aac, 1B_1 = 1B_2 = 0.0 Aac)$	ts	-	-	700	
Fall Time	t _f	-	-	90	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2%.

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D44VH10 (NPN), D45VH10 (PNP)

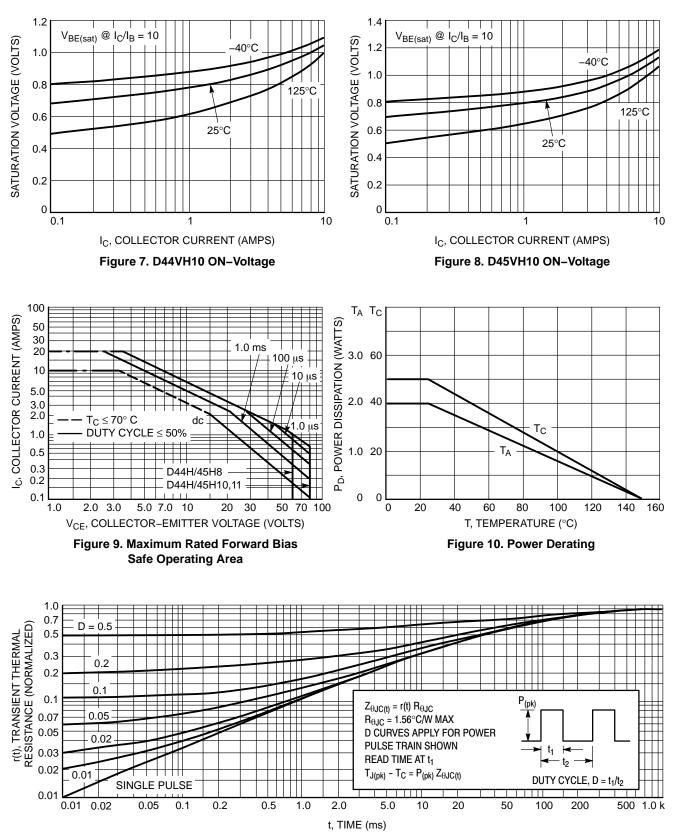
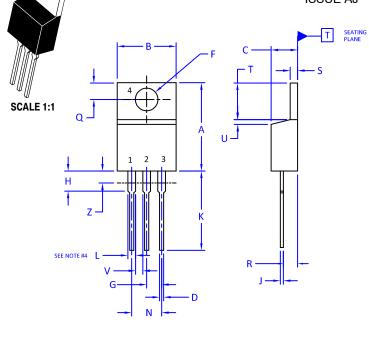


Figure 11. Thermal Response

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TO-220 CASE 221A-09 ISSUE AJ



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.

2. CONTROLLING DIMENSION: INCHES

3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCHES		MILLIMETERS		
DIM	MIN.	MAX.	MIN.	MAX.	
А	0.570	0.620	14.48	15.75	
В	0.380	0.415	9.66	10.53	
С	0.160	0.190	4.07	4.83	
D	0.025	0.038	0.64	0.96	
F	0.142	0.161	3.60	4.09	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.161	2.80	4.10	
J	0.014	0.024	0.36	0.61	
К	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
Ν	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.41	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045		1.15		
Z		0.080		2.04	

STYLE 1: PIN 1. 2. 3. 4.	COLLECTOR EMITTER	STYLE 2: PIN 1. 2. 3. 4.	EMITTER	3.	CATHODE ANODE GATE ANODE	STYLE 4: PIN 1. 2. 3. 4.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE MAIN TERMINAL 2
STYLE 5: PIN 1. 2. 3. 4.	DRAIN SOURCE	2. 3.	ANODE CATHODE ANODE CATHODE	2. 3.	CATHODE ANODE CATHODE ANODE	STYLE 8: PIN 1. 2. 3. 4.	••••••
STYLE 9: PIN 1. 2. 3. 4.	COLLECTOR EMITTER	STYLE 10: PIN 1. 2. 3. 4.	GATE SOURCE DRAIN	STYLE 11: PIN 1. 2. 3. 4.	DRAIN SOURCE GATE	STYLE 12 PIN 1. 2. 3. 4.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE NOT CONNECTED

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